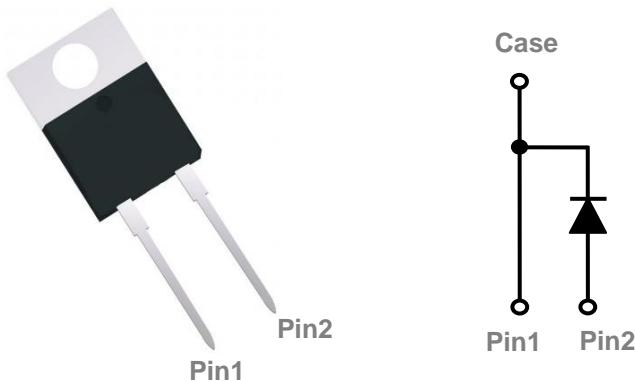


### General Description

These 650V high performance series of SiC schottky diodes are using the most advanced technology to suit for high frequency and high efficiency power systems with extreme low reverse recovery charge and can be stand up to 175°C maximum junction temperature.

### TO220-2L Pin Configuration



$V_{BR}$	$I_F$ ( $T_C = 154^\circ C$ )	$Q_C$
650V	8A	23nC

### Features

- 650V , 8A , 175°C junction temperature
- Extremely fast switching
- Ultra Low Reverse Recovery Current
- Positive temperature coefficient
- Green device available

### Applications

- Switching mode power supplies
- Motor drives
- Power Converters
- PFC, Power factor correction

### Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_R$	DC Peak Reverse Voltage, $T_j=25^\circ C$	650	V
$V_{RRM}$	Repetitive Peak Reverse Voltage, $T_j=25^\circ C$	650	V
$V_{RSM}$	Surge Peak Reverse Voltage, $T_j=25^\circ C$	650	V
$I_F$	Continuous Forward Current, $T_c=25^\circ C$	25	A
	Continuous Forward Current, $T_c=154^\circ C$	8	A
$I_{FSM}$	Non-Repetitive Forward Surge current $T_c = 25^\circ C$ , $T_p=10\text{ms}$ Half Sine Pulse	76	A
$T_J$	Maximum operating Junction Temperature Range	175	°C
$T_{STG}$	Storage Temperature Range	-55 to 175	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{eJC}$	Thermal Resistance Junction to Case	1.5	---	°C /W

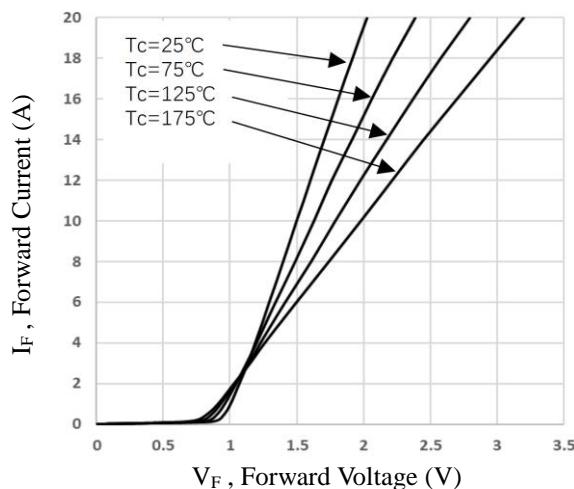
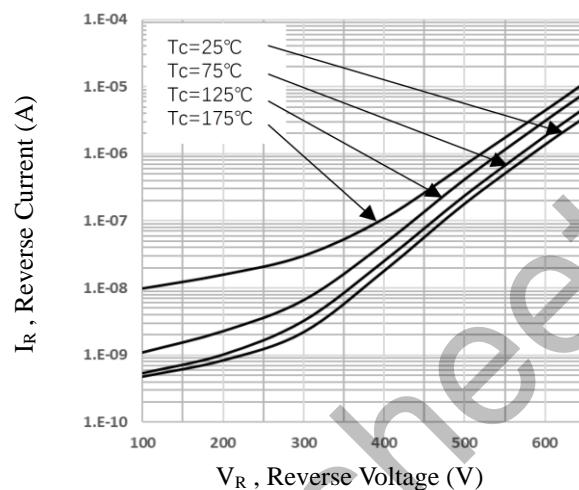
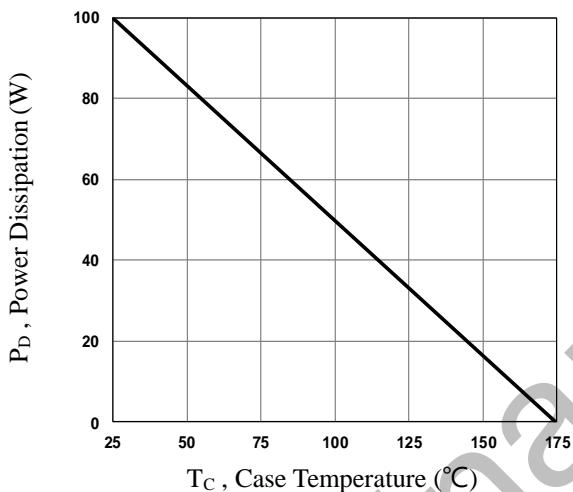
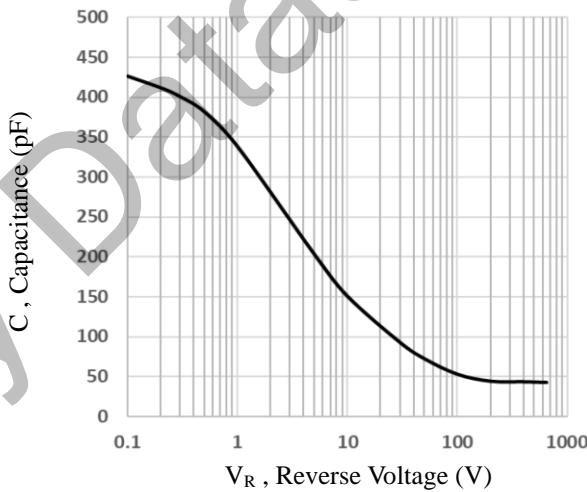


8A 650V Silicon Carbide Schottky Diode

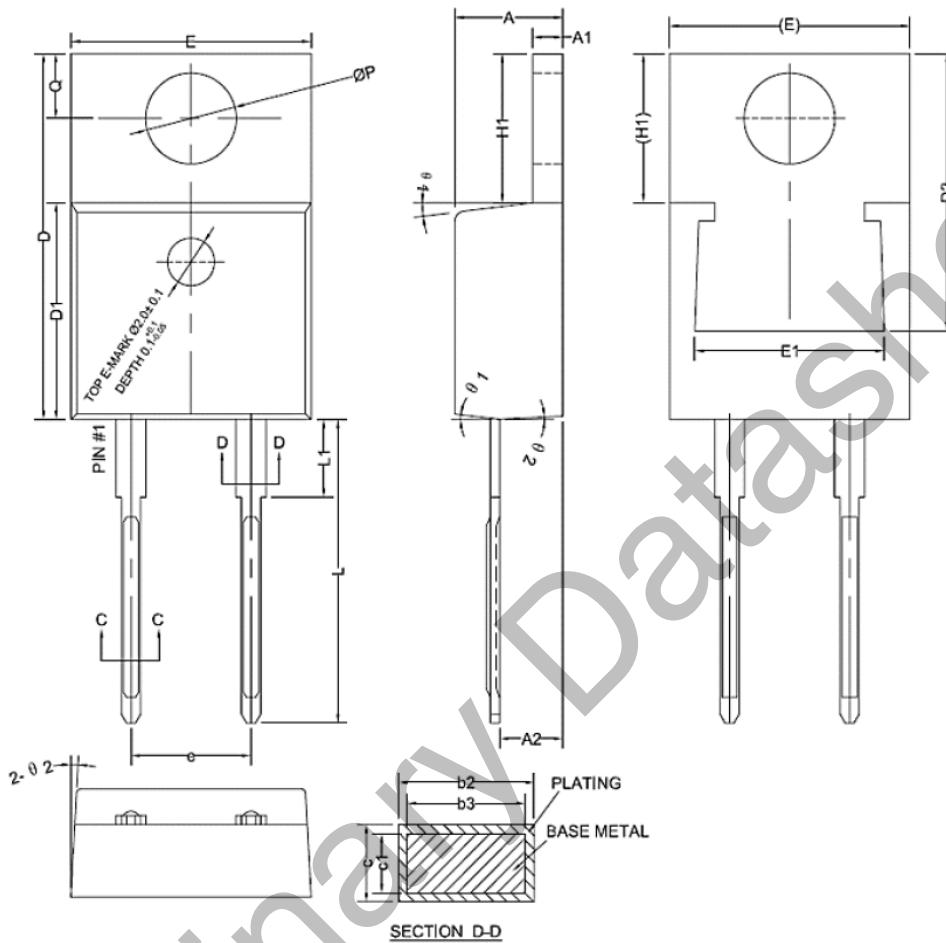
PCP08S065R

**Electrical Characteristics ( $T_J=25\text{ }^{\circ}\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
VDC	DC Blocking Voltage		650	---	---	V
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> =8A , T <sub>J</sub> =25°C	---	1.39	1.6	V
		I <sub>F</sub> =8A , T <sub>J</sub> =175°C	---	1.74	---	V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> =650V , T <sub>J</sub> =25°C	---	6	60	uA
		V <sub>R</sub> =650V , T <sub>J</sub> =175°C	---	12	---	uA
Q <sub>C</sub>	Total Capacitive Charge	V <sub>R</sub> =400V	---	23	---	nC
C	Total Capacitance	V <sub>R</sub> =1V, f=1MHz	---	338	---	pF
		V <sub>R</sub> =200V, f=1MHz	---	44	---	
		V <sub>R</sub> =400V, f=1MHz	---	43	---	


**Fig.1 Forward Characteristics**

**Fig.2 Reverse Characteristics**

**Fig.3 Power Dissipation**

**Fig.4 Capacitance Characteristics**

## TO220-2L PACKAGE INFORMATION



SYMBOL	mm			SYMBOL	mm		
	MIN	NOM	MAX		MIN	NOM	MAX
A	4.35	4.55	4.75	E	9.85	10.10	10.30
A1	1.25	---	1.35	E1	7.60	---	8.20
A2	2.2	2.6	2.8	e	4.90	5.10	5.20
b <sub>2</sub>	1.15	1.32	1.45	H <sub>1</sub>	6.35	6.45	6.55
b <sub>3</sub>	1.12	---	1.42	L	12.70	---	13.20
c	0.45	0.55	0.60	L <sub>1</sub>	2.80	---	3.40
c <sub>1</sub>	0.42	---	0.57	ΦP	3.30	3.60	3.85
D	15.15	15.50	16.00	Q	2.80	---	2.95
D <sub>1</sub>	9.05	9.15	9.25	θ <sub>1</sub>	5°	7°	9°
D <sub>2</sub>	12.20	---	14.00	θ <sub>1</sub>	1°	3°	5°